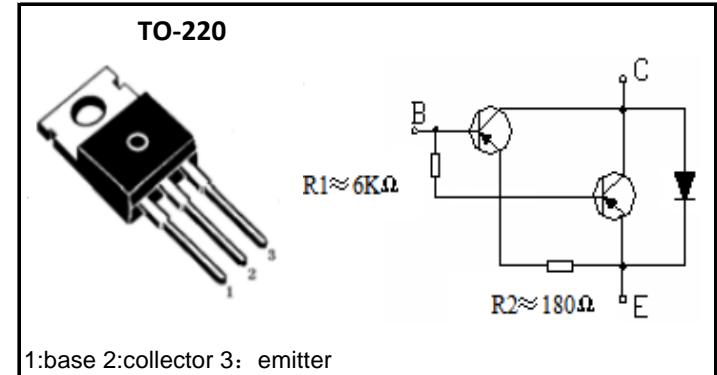


TIP127**FEATURES**

High current capability
High switching speed
Complementary to TIP122

Silicon PNP triode**Maximum ratings(Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	-100	V
Collector-Emitter Voltage	VCEO	-100	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current — Continuous	IC	-5	A
Collector Power Dissipation	Pc	2	W
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55~150	°C

Electrical Characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Base Sustaining Voltage	VCBO	IC=-0.1mA IB=0	-100		V
Collector-Emitter Sustaining Voltage	VCEO	IC=-10mA IB=0	-100		V
Emitter-Base Breakdown Voltage	VEBO	IE=-3mA IC=0	-5		V
Collector Cutoff Current	ICBO	VCB=-100V IE=0		-0.2	mA
Collector Cutoff Current	ICEO	VCE=-50V IB=0		-0.5	mA
Emitter Cutoff Current	IEBO	VEB=-5V IC=0		-2	mA
DC Current Gain	hFE	VCE=-3V IC=-500mA	1000		
		VCE=-5V IC=-3A	1000	15000	
Collector-Emitter Saturation Voltage	VCE(sat)	IC=-3A IB=-12mA		-2	V
		IC=-5A IB=-20mA		-4	V
Collector-Base Saturation Voltage	VBE(sat)	IC=-3A IB=-12mA		-2.5	V
Base-Emitter On Voltage	VBE(on)	VCE=-3V IC=-3A		-2.5	V